

Supporting Information

## **Armoring SiO<sub>x</sub> with a Conformal LiF Layer to Boost Lithium Storage**

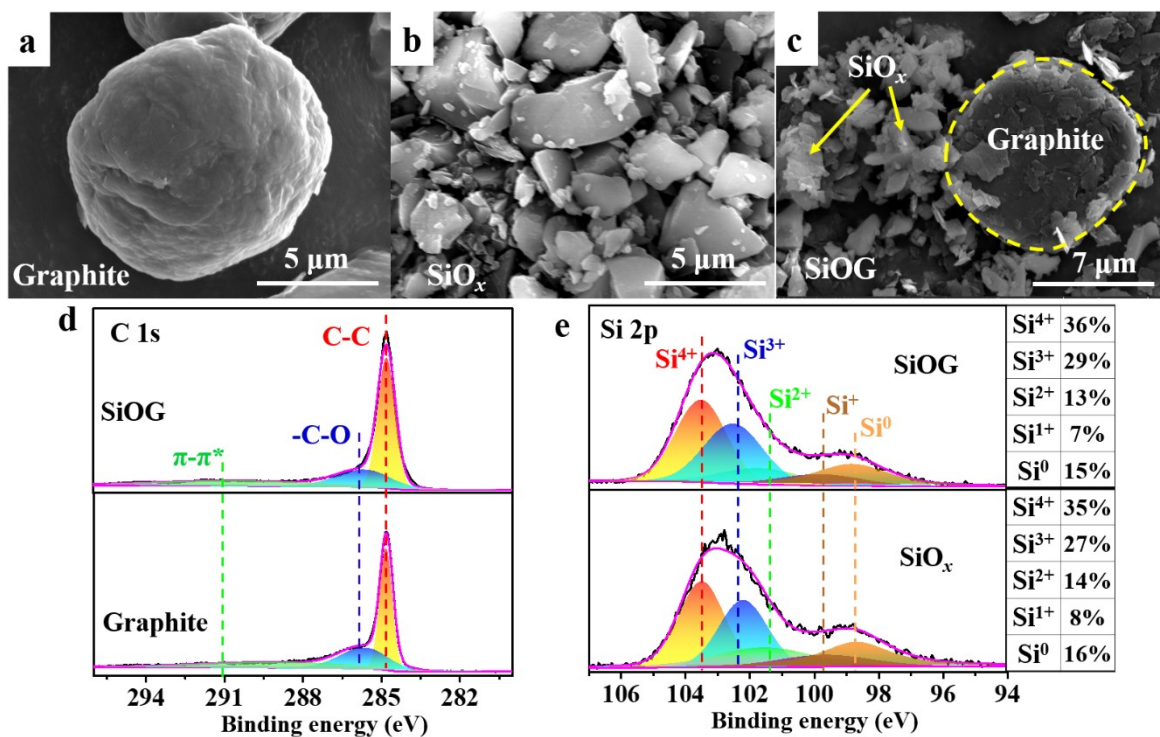
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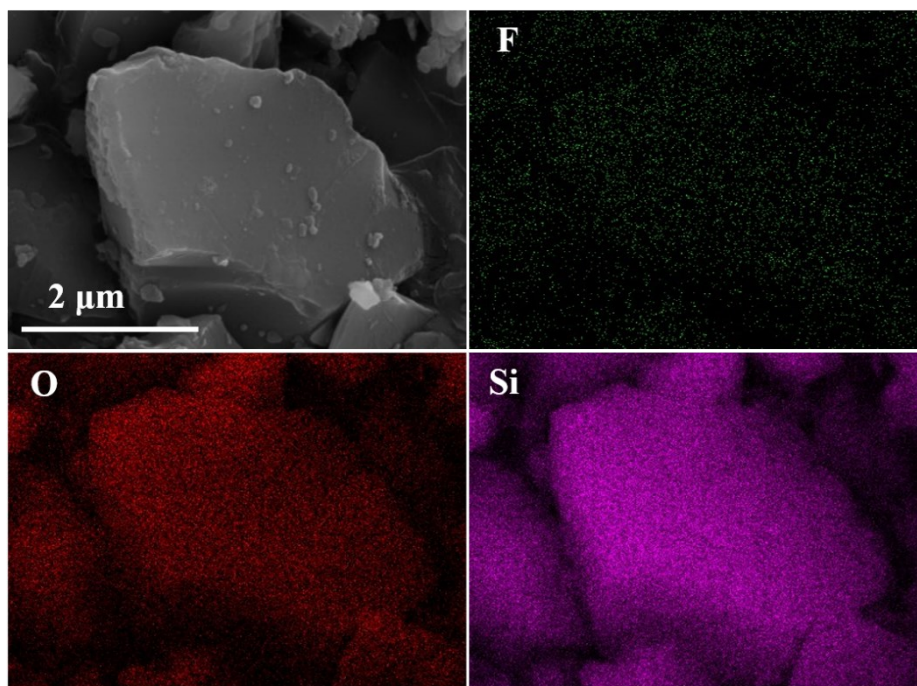
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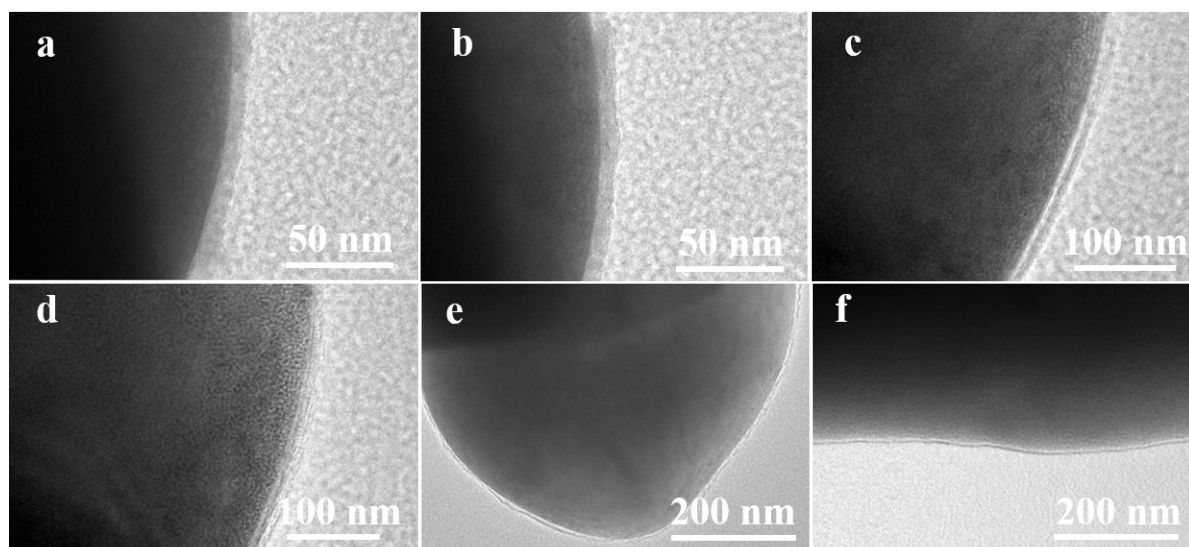
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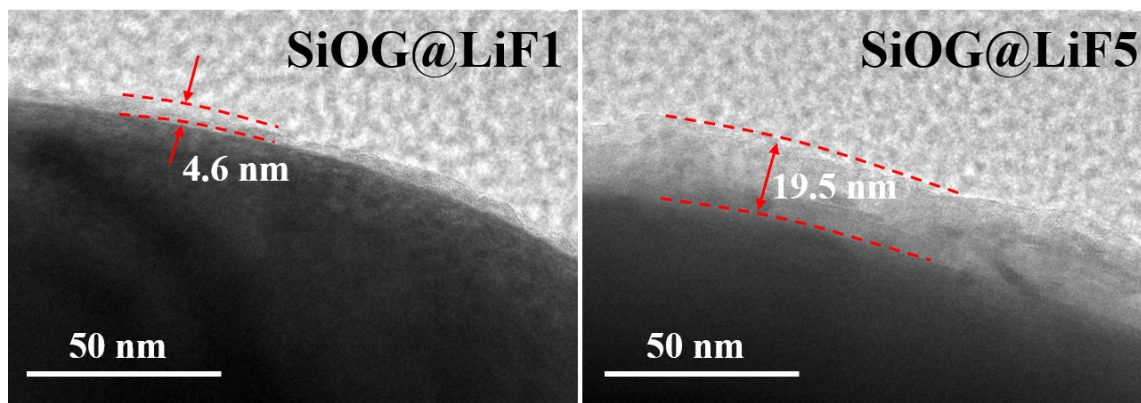
**Figure S1.** (a, b, c) SEM images of graphite, SiO<sub>x</sub> and SiOG. (d) High resolution C 1s XPS spectra of SiOG and graphite. (e) High resolution Si 2p XPS spectra and content of Si in different valence of SiO<sub>x</sub> and SiOG.



**Figure S2.** SEM images and corresponding element mappings of Si, O and F in SiOG@LiF<sub>3</sub>.



**Figure S3.** TEM images of SiOG@LiF3 at different magnifications.



**Figure S4.** TEM images of SiOG@LiF1 and SiOG@LiF5.

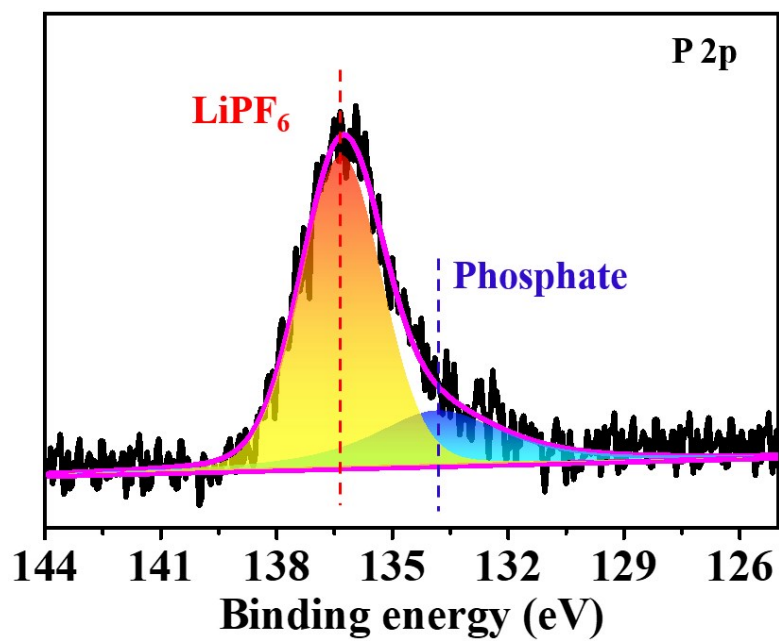
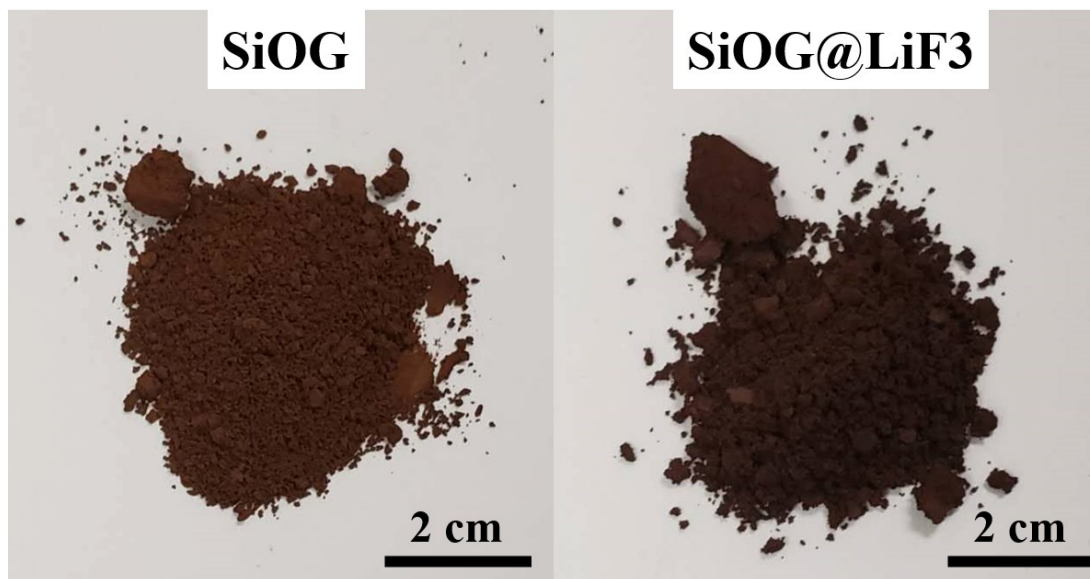
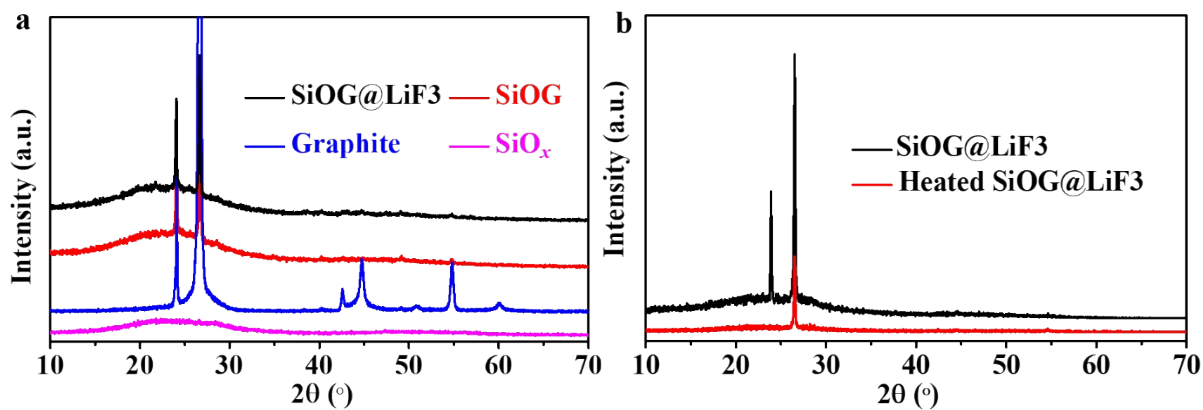


Figure S5. High resolution P 2p of sample SiOG@LiF3 after heating.

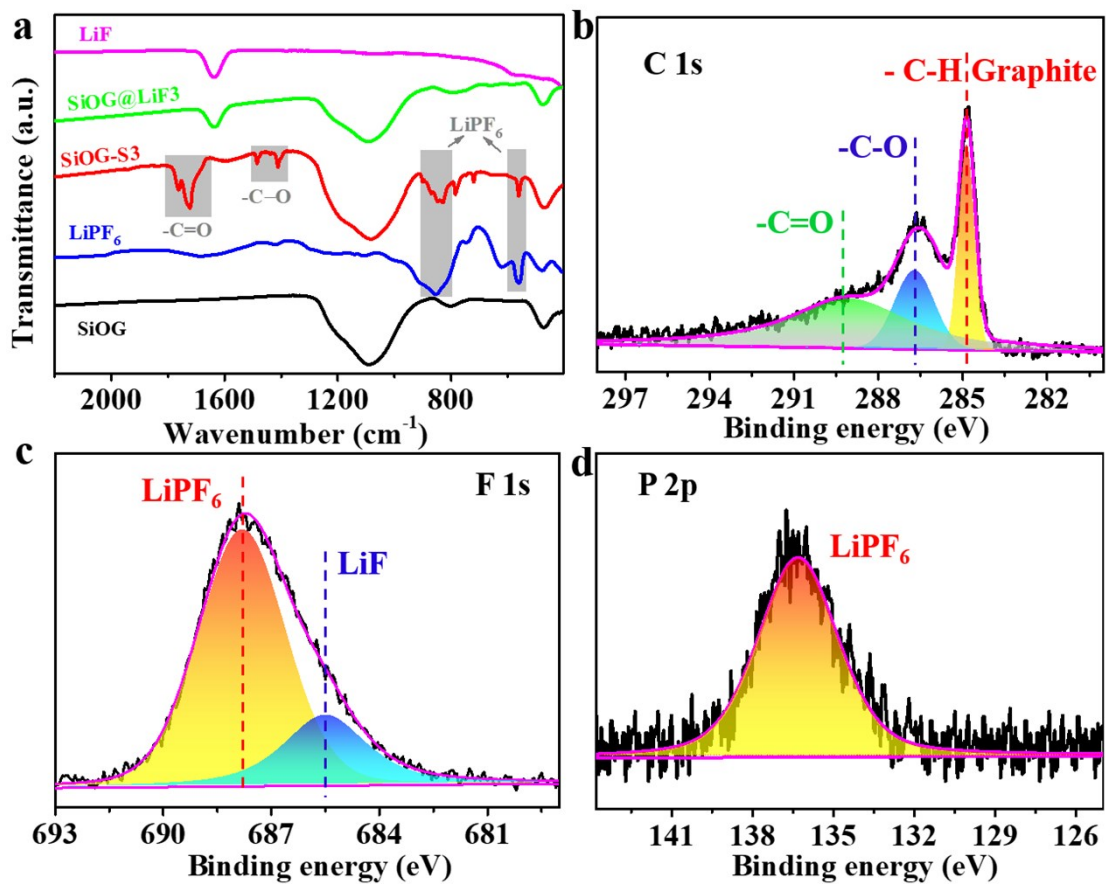


**Figure S6.** Digital images of SiOG and SiOG@LiF3 powder.

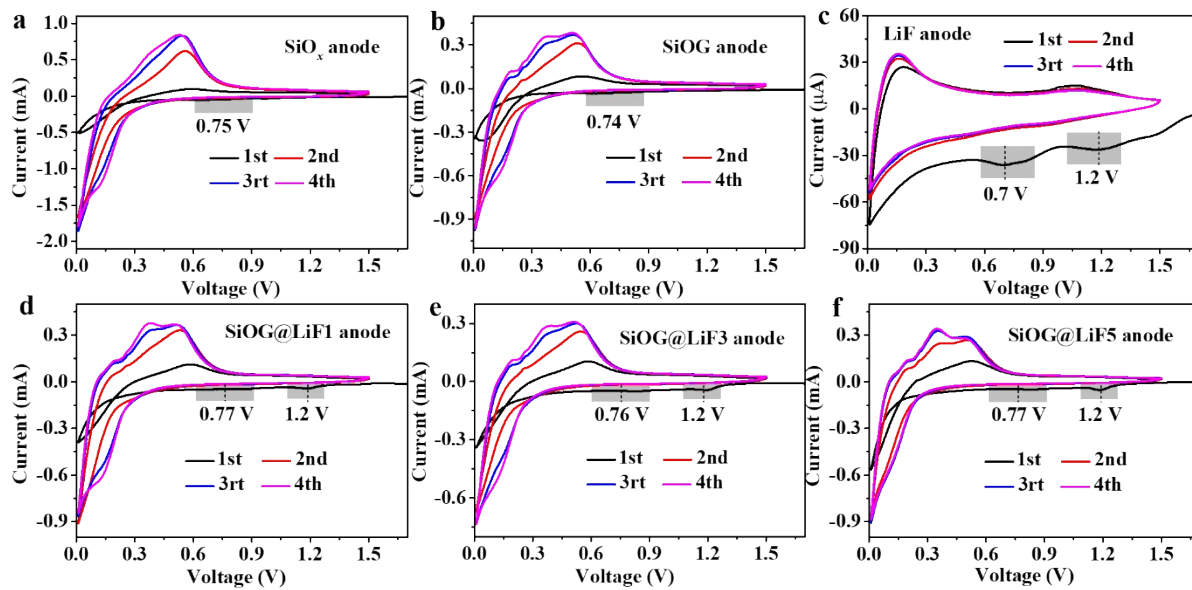


**Figure S7.** (a) XRD pattern of SiO<sub>x</sub>, graphite, SiOG and SiOG@LiF<sub>3</sub>. (b) XRD patterns of SiOG@LiF<sub>3</sub> before and after heating.

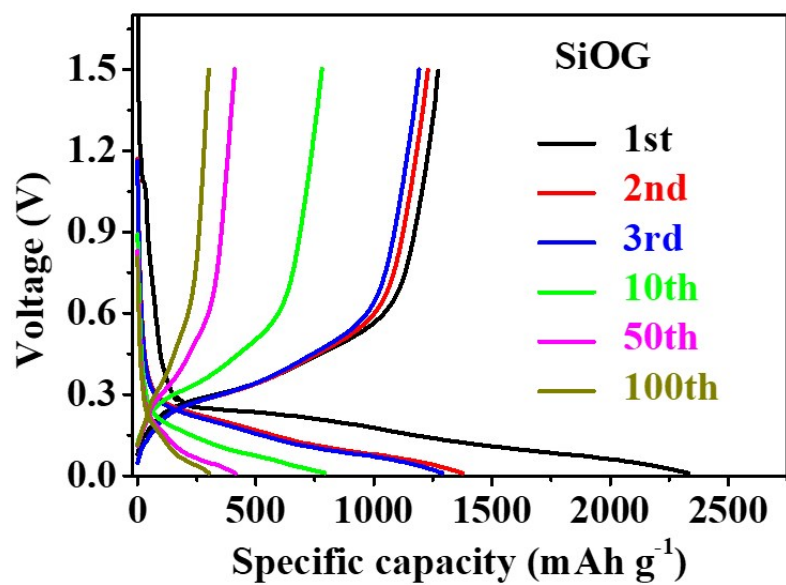




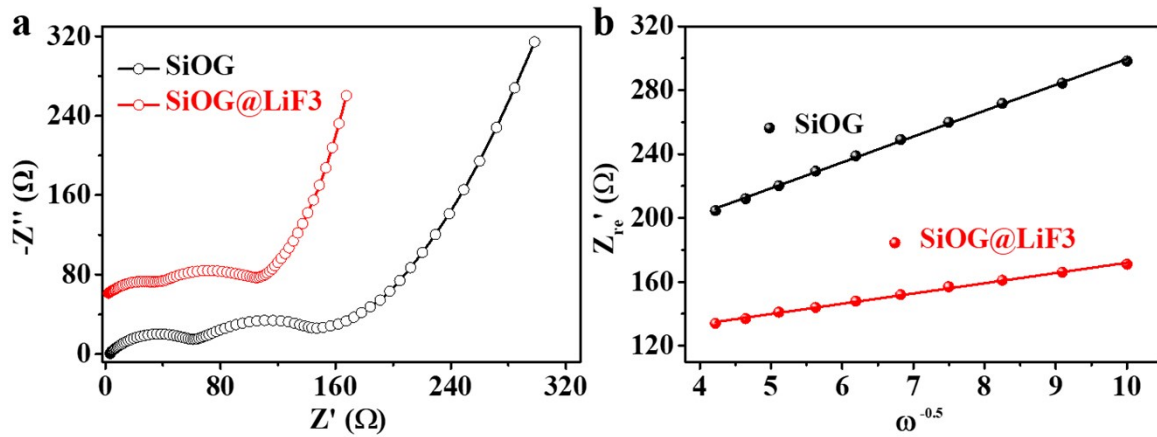
**Figure S8.** (a) FTIR results of samples LiF, SiOG@LiF<sub>3</sub>, SiOG-S3, LiPF<sub>6</sub> and SiOG; (b, c, d) C 1s, F 1s and P 2p of sample SiOG-S3.



**Figure S9.** CV curves of (a)  $\text{SiO}_x$ , (b) SiOG, (c) LiF anode, (d) SiOG@LiF1, (e) SiOG@LiF3 and (f) SiOG@LiF5. The scan rate is  $0.1 \text{ mV s}^{-1}$ .

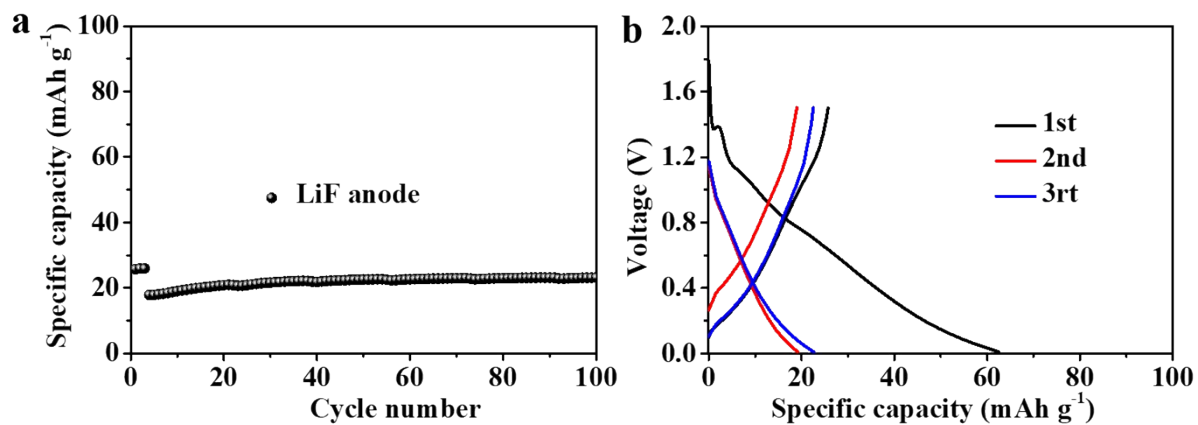


**Figure S10.** Typical charge/discharge profiles of sample SiOG under 500 mA g<sup>-1</sup> and 100 mA g<sup>-1</sup> for the first three cycles.

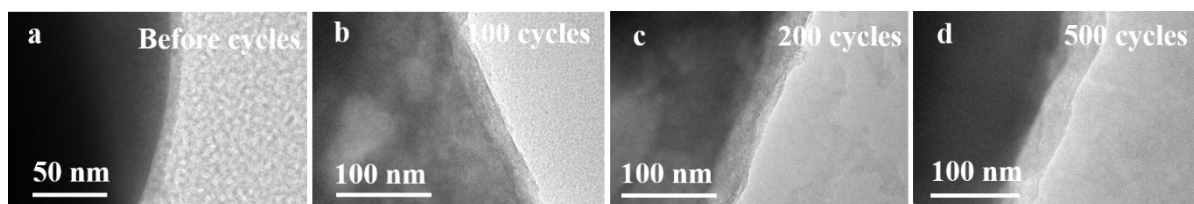


**Figure S11.** (a) Nyquist plots of SiOG and SiOG@LiF3 electrodes after 1 cycle. (b) Linear relationship between real impedance and reciprocal square root of low-angular frequency.

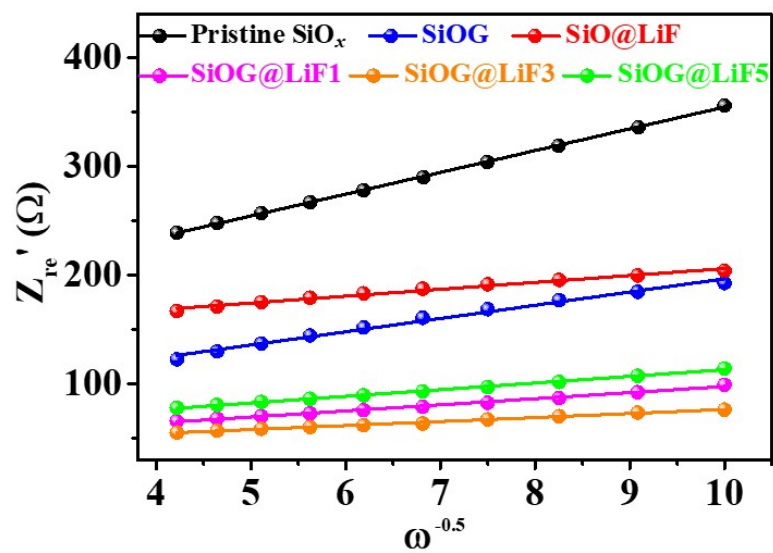
The lithium ion diffusion coefficient ( $D_{Li^+}$ ) can be calculated according to the equations ( $Z_{re} = R_e + R_f + R_{ct} + \sigma_w \omega^{-0.5}$ ;  $D_{Li^+} = 0.5(RT/AF^2\sigma_w C)^2$ ), where  $R$ ,  $T$ ,  $A$ ,  $F$ , and  $C$  are gas constant, absolute temperature, surface area of electrode, Faraday constant and the concentration of lithium ion, respectively.<sup>1</sup> Figure S8a and S8b shows the Nyquist plots of SiOG and SiOG@LiF3 electrodes after 1 cycle and corresponding linear relationship between  $Z'_{re}$  and  $\omega^{-0.5}$  where the Warburg coefficient  $\sigma_w$  can be derived according to above equations. Therefore, the calculated  $D_{Li^+}$  of SiOG and SiOG@LiF3 after 1 cycle are  $7.28 \times 10^{-14}$  and  $5.38 \times 10^{-13}$   $\text{cm}^2 \text{s}^{-1}$  respectively.



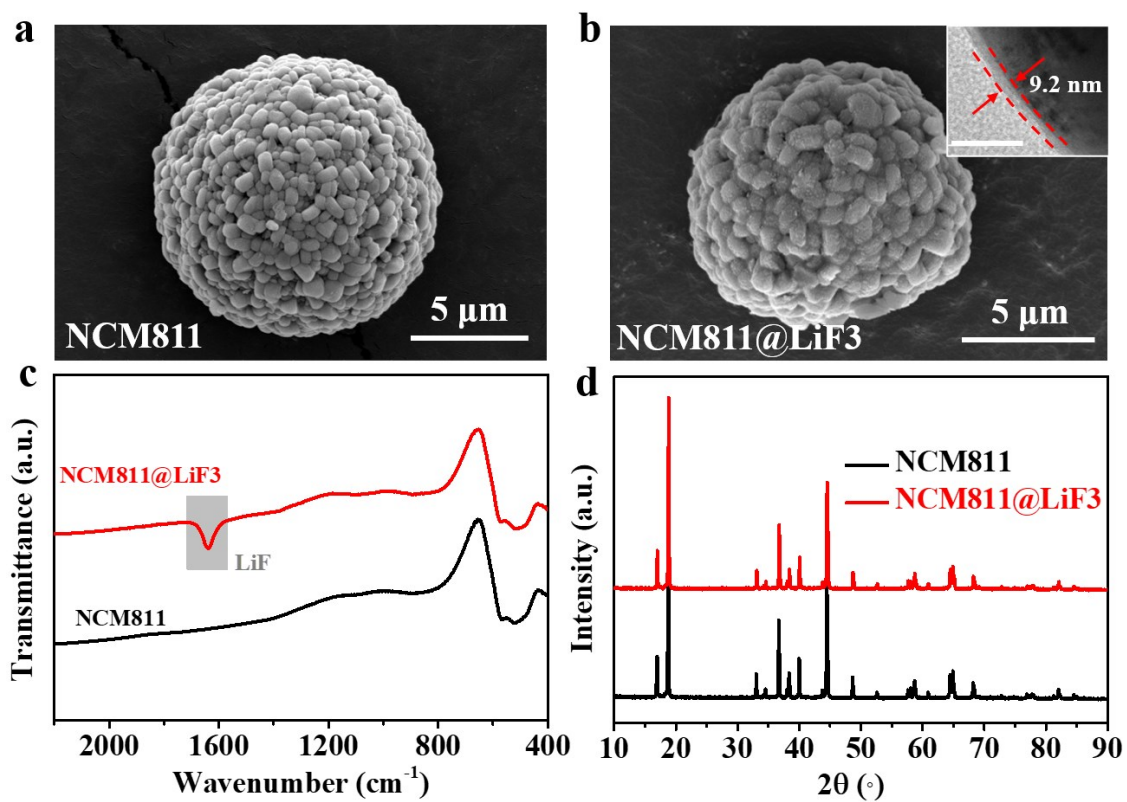
**Figure S12.** Cycling stability (a) and typical charge/discharge profiles (b) of LiF anode under 500 mA g<sup>-1</sup> and 100 mA g<sup>-1</sup> for the first three cycles.



**Figure S13.** (a-d) TEM images of SiOG@LiF3 sample before cycle, after 100 cycles, 200 cycles and 500 cycles.

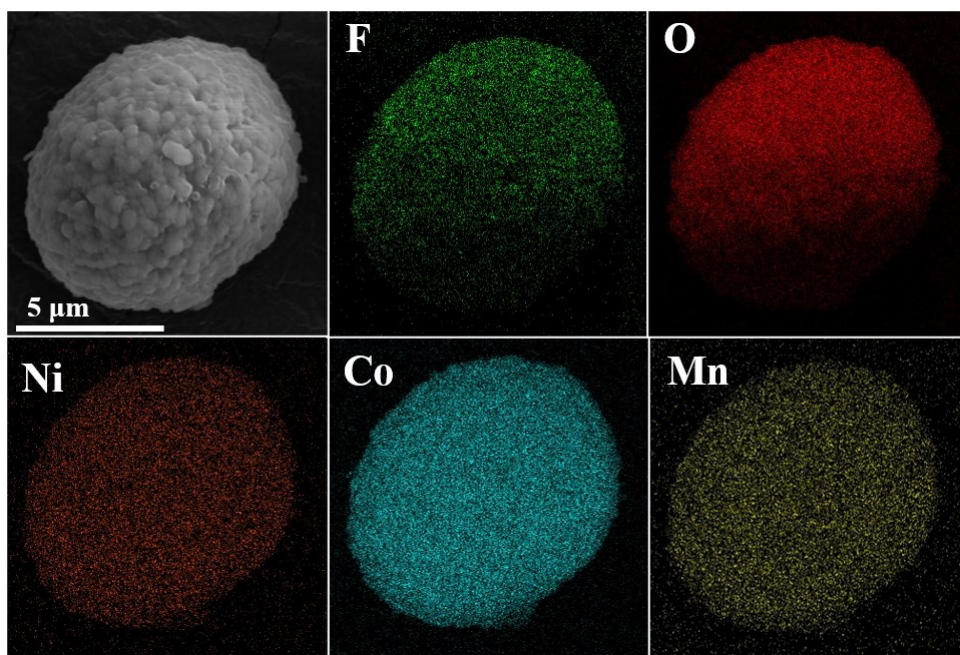


**Figure S14.** Linear relationship between real impedance and reciprocal square root of low-angular frequency.

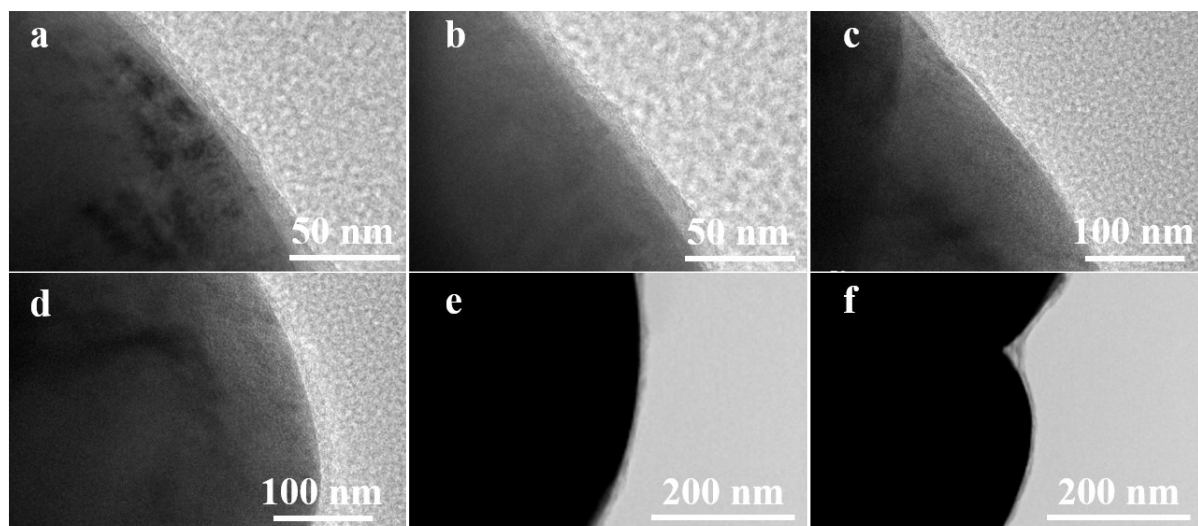


**Figure S15.** SEM images (a, b), FTIR spectrum (c) and XRD patterns (d) of NCM811 and NCM811@LiF3. The inset in Figure S6b is a TEM image of NCM811@LiF3 and the scale bar is 50 μm.

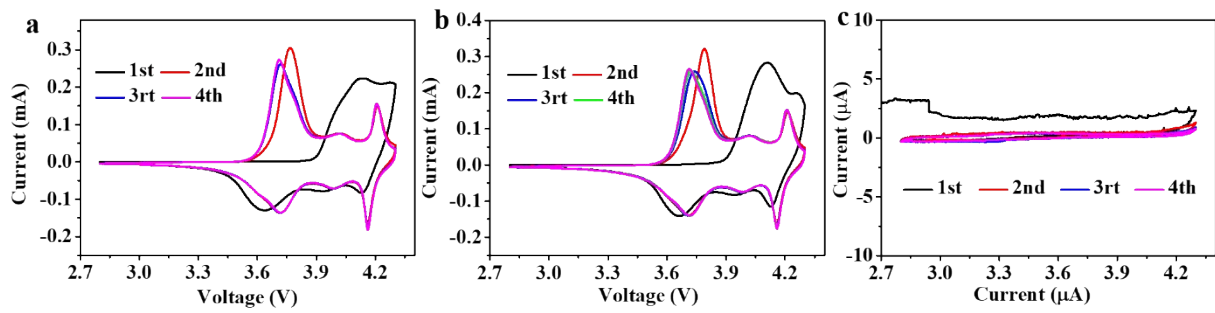




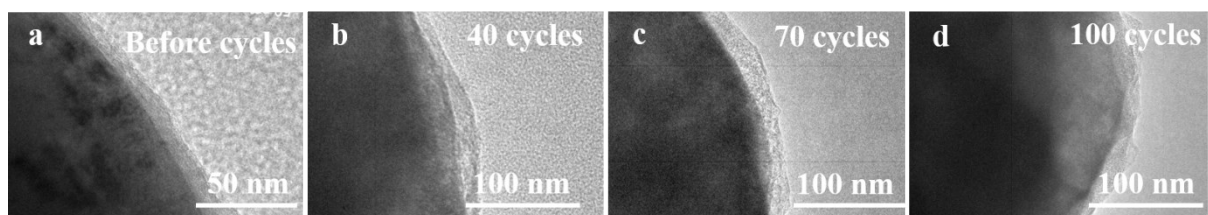
**Figure S16.** SEM images and corresponding element mappings of F, O, Ni, Co and Mn in NCM811@LiF<sub>3</sub>.



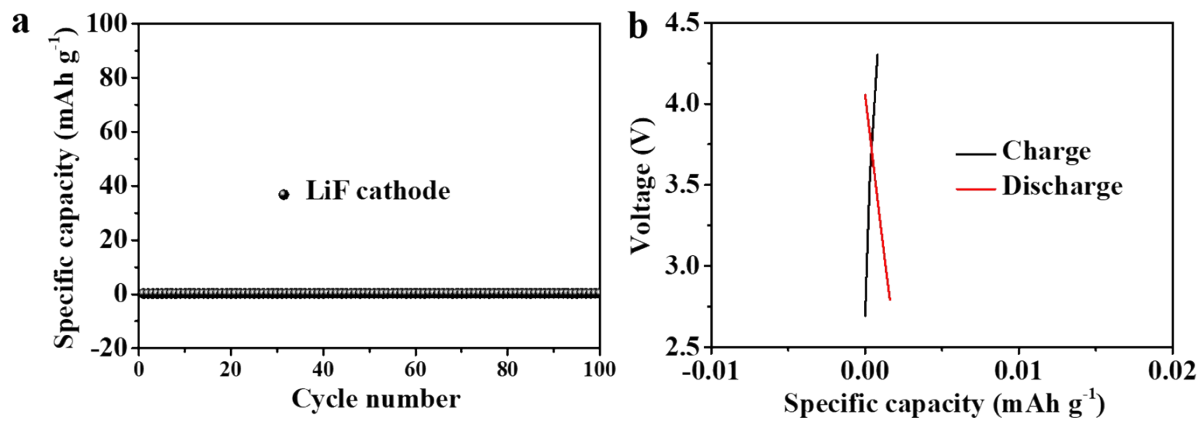
**Figure S17.** TEM images of NCM811@LiF3 at different magnifications.



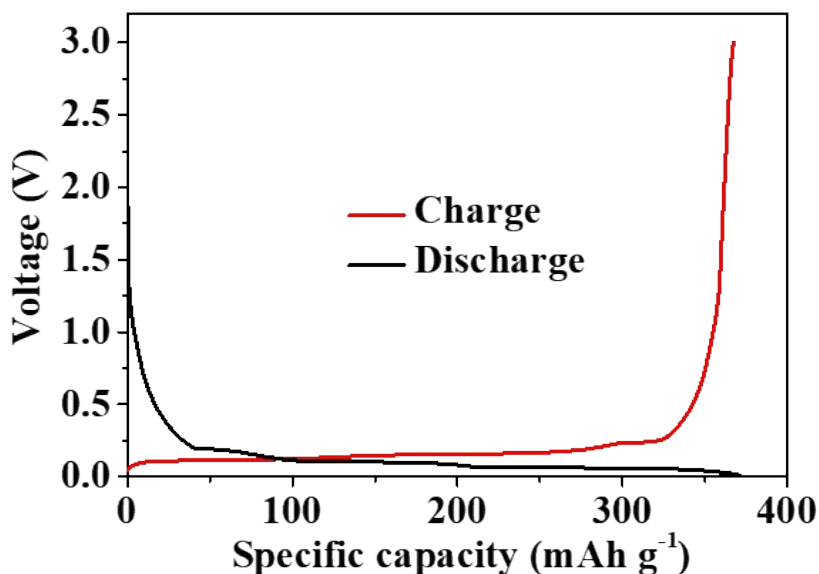
**Figure S18.** CV curves of (a) NCM811, (b) NCM811@LiF3 and (c) LiF cathode. The scan rate is  $0.1 \text{ mV s}^{-1}$ .



**Figure S19.** (a-d) TEM images of NCM811@LiF3 sample before cycling, after 40, 70 and 100 cycles.



**Figure S20.** Cycling stability (a) and typical charge/discharge profiles (b) of LiF cathode under 100 mA g<sup>-1</sup>.



**Figure S21.** The 1<sup>st</sup> charge/discharge curves of graphite anode.

**Note 1.** The portion of  $\text{SiO}_x$  of whole  $\text{SiO}_x$  joined in the electrochemical events can be calculated as the equation:  $P = D_a/D_t$ , where  $P$  is the portion of  $\text{SiO}_x$  of whole  $\text{SiO}_x$  joined in the electrochemical events,  $D_a$  is the actual initial discharge capacity of  $\text{SiO}_x$  in  $\text{SiOG@LiF}_3$  anode,  $D_t$  is the theoretical specific capacity of  $\text{SiO}_x$  ( $\sim 2680 \text{ mAh g}^{-1}$ <sup>12</sup>). The 1<sup>st</sup> discharge capacity of  $\text{SiOG@LiF}_3$  anode is  $2065 \text{ mAh g}^{-1}$ , and 1<sup>st</sup> discharge capacity of graphite anode is  $371 \text{ mAh g}^{-1}$ . Given that the content of graphite in  $\text{SiOG}$  sample is 10 wt% (the corresponding  $\text{SiO}_x$  content is 90%),  $D_a$  of  $\text{SiOG@LiF}_3$  anode is  $2253 \text{ mAh g}^{-1}$  ( $(2065-371*10\%)/90\%$ ). Therefore, the calculated  $P$  of  $\text{SiOG@LiF}_3$  anode is 84.1%, which means about 84.1% of whole  $\text{SiO}_x$  joined the electrochemical events. Note that the capacity contribution of  $\text{LiF}$  can be ignored due to its low capacity (Figure S12) and low content.

**Table S1.** Comparison of the rate performance between SiO<sub>x</sub>-based materials reported recently.

Materials	Current density (mA g <sup>-1</sup> )	Capacity (mAh g <sup>-1</sup> )	Ref.
SiO <sub>x</sub> /C-2	200	792	2
	600	620	
Sn <sub>2</sub> Fe@30SiO <sub>x</sub>	200	710	3
	2000	570	
SiO <sub>x</sub> /G/C	300	750	4
	3000	592	
SiO <sub>x</sub> -TiO <sub>2</sub> @C	200	916	1
	3200	542	
SiO <sub>x</sub> /C	325	645	5
	3250	549	
SiO <sub>x</sub> /TiO <sub>2</sub> @MLG	200	1052	6
	5000	429	
SiO <sub>x</sub> /C-CVD	200	1120	7
	5000	410	
SiO <sub>x</sub> @C	200	1117	8
	5000	426	
SiO <sub>x</sub> @G	500	1100	9
	5000	795	
C-SiO <sub>x</sub> /C	300	1410	10
	7500	1191	
SiO <sub>x</sub> @TiO <sub>2</sub> @C	500	1440	11
	5000	1146	
SiOG@LiF3	200	1276	This work
	5000	741	

**Table S2.** Combined interfacial resistance and  $D_{\text{Li}^+}$  of pristine  $\text{SiO}_x$ ,  $\text{SiO@LiF}_3$ ,  $\text{SiOG}$ ,  $\text{SiOG@LiF}_1$ ,  $\text{SiOG@LiF}_3$  and  $\text{SiOG@LiF}_5$  after 100 cycles

<b>Samples</b>	<b>Pristine <math>\text{SiO}_x</math></b>	<b><math>\text{SiO@LiF}_3</math></b>	<b><math>\text{SiOG}</math></b>	<b><math>\text{SiOG@LiF}_1</math></b>	<b><math>\text{SiOG@LiF}_3</math></b>	<b><math>\text{SiOG@LiF}_5</math></b>
<b><math>R_1</math> (<math>\Omega</math>)</b>	103.93	56.48	38.25	15.89	13.84	16.55
<b><math>R_2</math> (<math>\Omega</math>)</b>	133.25	69.26	40.77	22.75	16.28	35.38
<b>Combined interfacial resistance</b>	237.18	125.74	79.02	38.64	30.12	51.93
<b><math>D_{\text{Li}^+} \times 10^{-13}</math> (<math>\text{cm}^2 \text{s}^{-1}</math>)</b>	0.58	5.8	0.89	7.3	9.13	7.42



**Table S3.** Calculated HOMO/LUMO energy levels and energy gap of electrolyte compounds (EC, EC, DMC, FEC and LiPF<sub>6</sub>)

<b>Samples</b>		<b>EMC</b>	<b>EC</b>	<b>DMC</b>	<b>FEC</b>	<b>LiPF<sub>6</sub></b>
<b>Energy (eV)</b>	<b>LUMO</b>	1.21	1.07	1.15	0.52	-1.61
	<b>HOMO</b>	-7.63	-8.02	-7.70	-8.44	-10.01
<b>GAP (eV)</b>		8.84	9.09	8.85	8.96	8.40

## References

1. Z. Li, H. Zhao, P. Lv, Z. Zhang, Y. Zhang, Z. Du, Y. Teng, L. Zhao and Z. Zhu, *Adv. Funct. Mater.*, 2018, **28**, 1605711.
2. Z. Liu, D. Guan, Q. Yu, L. Xu, Z. Zhuang, T. Zhu, D. Zhao, L. Zhou and L. Mai, *Energy Storage Materials*, 2018, **13**, 112-118.
3. H. Zhang, R. Hu, Y. Liu, X. Cheng, J. Liu, Z. Lu, M. Zeng, L. Yang, J. Liu and M. Zhu, *Energy Storage Materials*, 2018, **13**, 257-266.
4. G. Li, J.Y. Li, F.S. Yue, Q. Xu, T.T. Zuo, Y.X. Yin and Y.G. Guo, *Nano Energy*, 2019, **60**, 485-492.
5. Q. Xu, J.K. Sun, Y.X. Yin and Y.G. Guo, *Adv. Funct. Mater.*, 2018, **28**, 1705235.
6. H. Xue, Y. Wu, Y. Zou, Y. Shen, G. Liu, Q. Li, D. Yin, L. Wang and J. Ming, *Adv. Funct. Mater.*, 2020, **30**, 1910657.
7. Z. Liu, Y. Zhao, R. He, W. Luo, J. Meng, Q. Yu, D. Zhao, L. Zhou and L. Mai, *Energy Storage Materials*, 2019, **19**, 299-305.
8. Z. Li, H. Zhao, J. Wang, T. Zhang, B. Fu, Z. Zhang and X. Tao, *Nano Res.*, 2020, **13**, 527-532.
9. Q. Xu, J. K. Sun, Z. L. Yu, Y. X. Yin, S. Xin, S. H. Yu and Y. G. Guo, *Adv. Mater.*, 2018, **30**, 1707430.
10. G. Li, L.B. Huang, M.Y. Yan, J.Y. Li, K.C. Jiang, Y.X. Yin, S. Xin, Q. Xu and Y.G. Guo, *Nano Energy*, 2020, **74**, 104890.
11. Z. Xiao, C. Yu, X. Lin, X. Chen, C. Zhang, H. Jiang, R. Zhang and F. Wei, *Nano Energy*, 2020, **77**, 105082.
12. D. He, P. Li, W. A. Wang, Q. Wan, J. Zhang, K. Xi, X. Ma, Z. Liu, L. Zhang and X. Qu, *Small*, 2020, **16**, 1905736.